

/ Descriptions

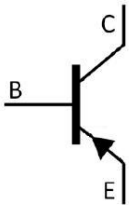
TO-126

PNP

Silicon PNP transistor in a TO-126 Plastic Package.

/ Features V_{CEO} High V_{CEO} Large DC current, high f_T , low $V_{CE(sat)}$.**/ Applications**

Low power audio amplifier, high speed switching applications.

/ Equivalent Circuit**/ Pinning**

PIN1 Emitter

PIN 2 Collector

PIN 3 Base

/ h_{FE} Classifications & Marking

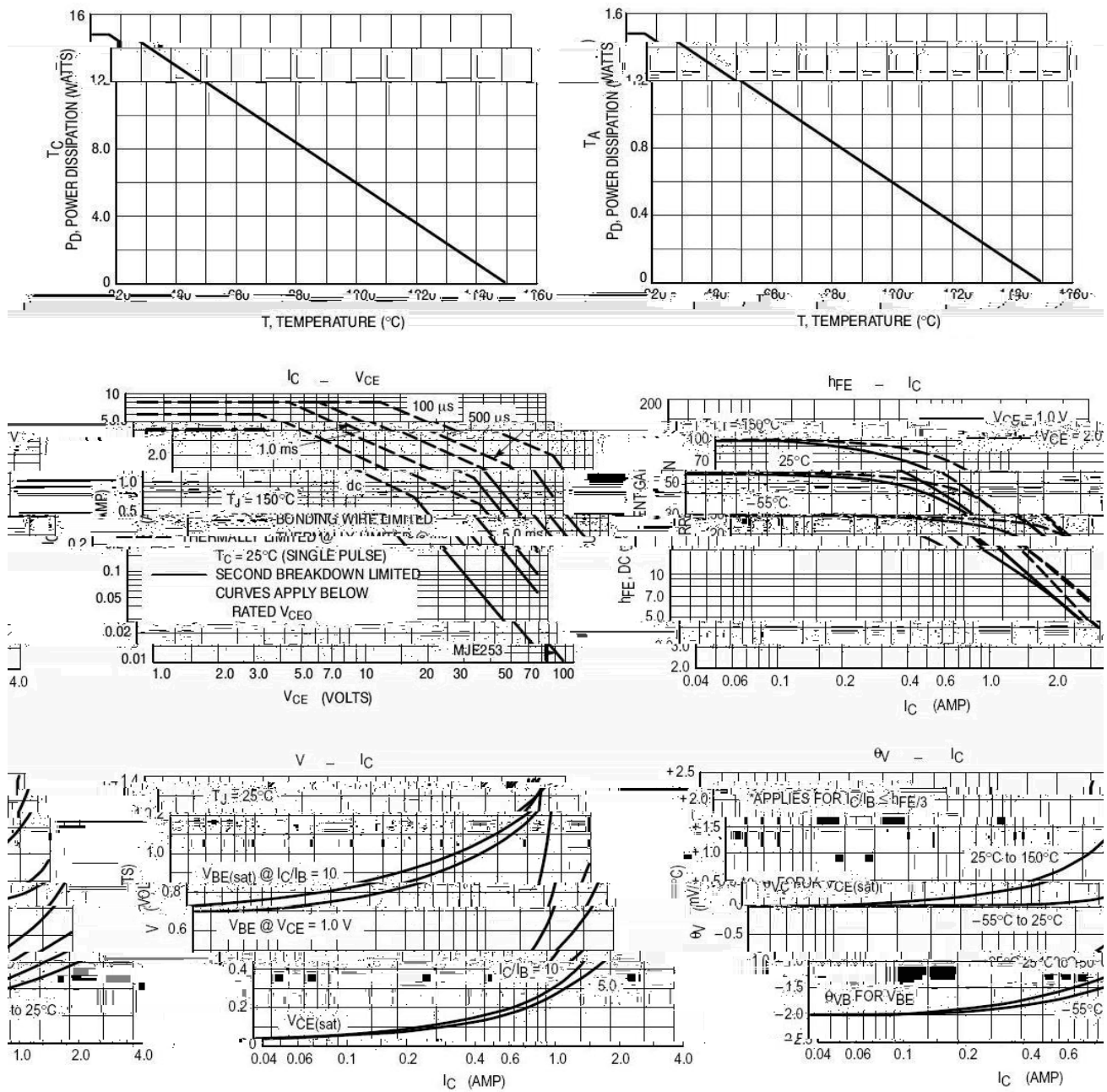
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	$I_{C(1)}$	-4.0	A
	$I_{C(2)}$	-8.0	A
Peak Collector Current	I_B	-10	A
Collector Power Dissipation	P_D	1.5	W
Collector Power Dissipation	$P_D(T_c=25^{\circ}C)$	15	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-100			V
Collector Cut-Off Current	$I_{CBO(1)}$	$V_{CB}=-100V$ $I_E=0$			-0.1	μA
	$I_{CBO(2)}$	$V_{CE}=-100V$ $T_c=125^{\circ}C$			-0.1	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-7.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-200mA$	40		180	
	$h_{FE(2)}$	$V_{CE}=-1.0V$ $I_C=-1.0A$	15			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-500mA$ $I_B=-50mA$			-0.3	V
	$V_{CE(sat)(2)}$	$I_C=-1.0A$ $I_B=-100mA$			-0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-2.0A$ $I_B=-200mA$			-1.8	V
Base to Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=-1.0V$ $I_C=-500mA$			-1.5	V

BE(on)

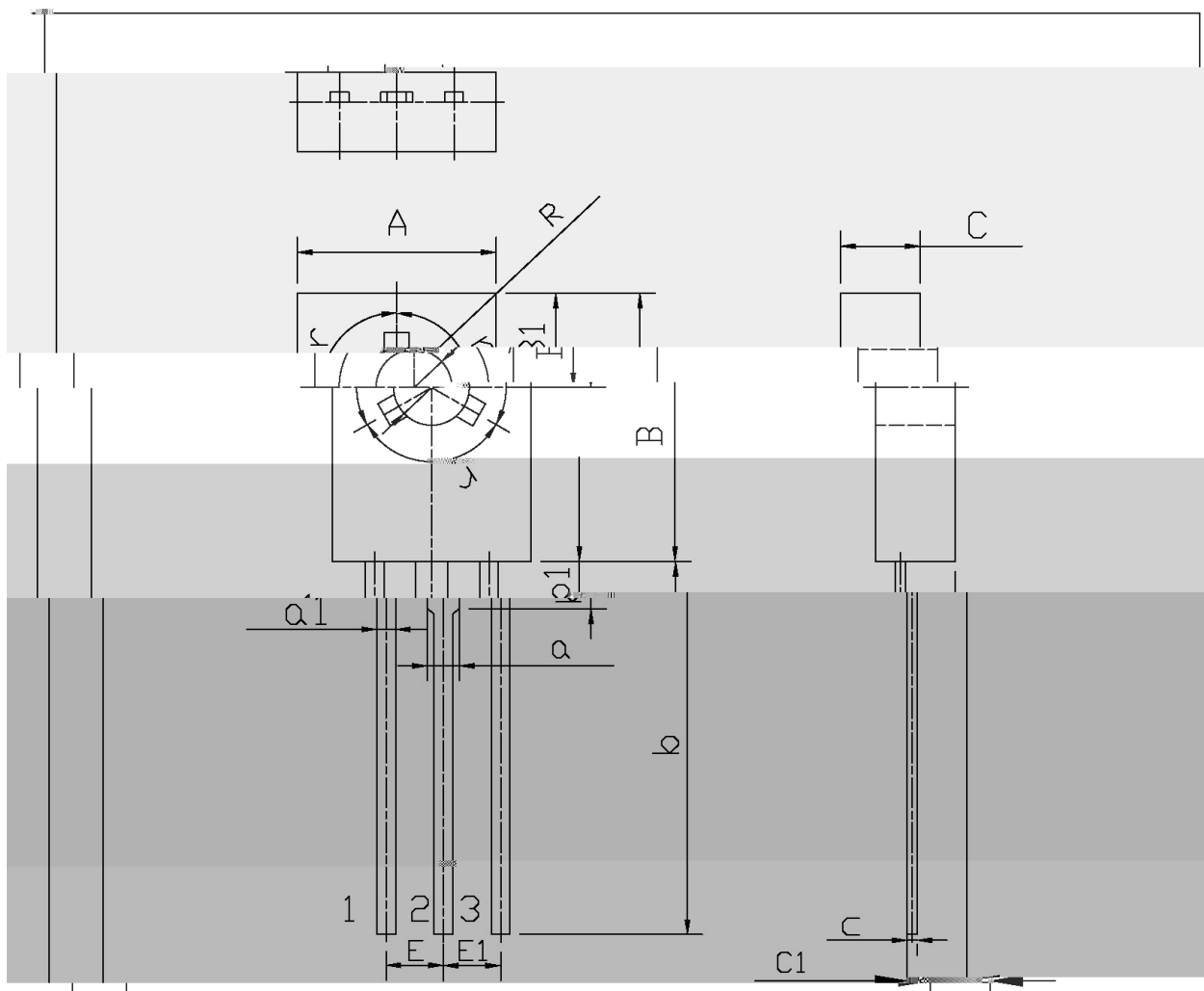
/ Electrical Characteristic Curve



/ Package Dimensions

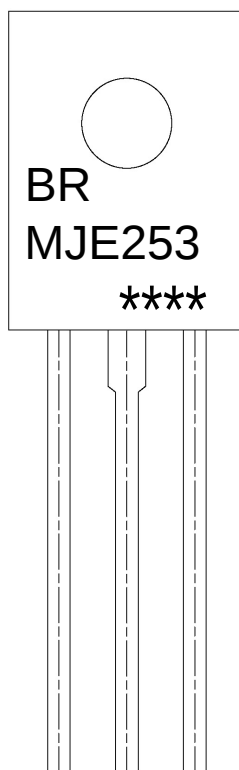
T□-126

单位: mm



Dimension	Symbol	Value	Unit
Width of main body	A	12.6	mm
Height of main body	B	10.0	mm
Width of mounting tab	C	5.0	mm
Distance from center of mounting holes to edge of main body	A1	6.3	mm
Distance between centers of mounting holes	a	10.0	mm
Distance from center of mounting holes to edge of mounting tab	a1	10.0	mm
Width of mounting holes	E	2.5	mm
Distance between centers of mounting holes	E1	10.0	mm
Width of mounting tab at base	C1	5.0	mm
Radius of mounting holes	R	1.25	mm

/ Marking Instructions



BR

MJE253

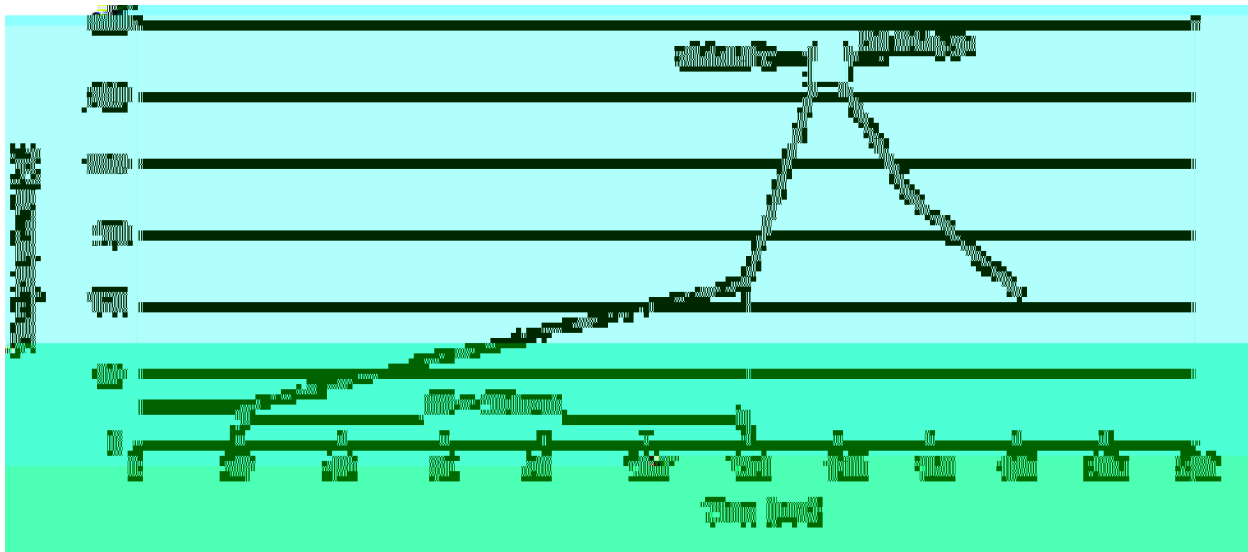
Note:

BR: Company Code

MJE253: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5℃ Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-126/F	65	26	1,690	5	8,450	532×31×5.6	555×164×50	575×290×180